2SK2906-01

FUJI POWER MOS-FET

N-CHANNEL SILICON POWER MOS-FET

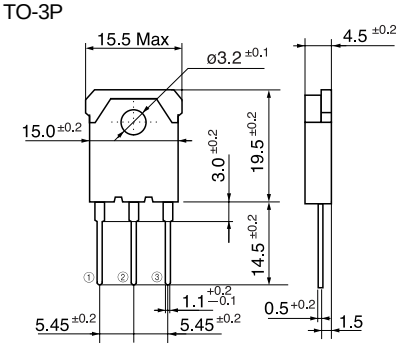
■ Features

High speed switching
Low on-resistance
No secondary breadown
Low driving power
Avalanche-proof

■ Applications

Switching regulators
UPS (Uninterruptible Power Supply)
DC-DC converters

TO-3P



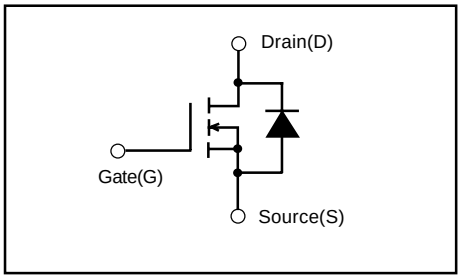
■ Maximum ratings and characteristic Absolute maximum ratings

● **(Tc=25°C unless otherwise specified)**

Item	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	60	V
Continuous drain current	I_D	±100	A
Pulsed drain current	$I_{D(puls)}$	±400	A
Gate-source voltage	V_{GS}	±30	V
Maximum Avalanche Energy	E_{AV}*1	1268.3	mJ
Max. power dissipation	P_D	150	W
Operating and storage	T_{ch}	+150	℃
temperature range	T_{stg}	-55 to +150	℃

*1 L=0.169mH, Vcc=24V

■ Equivalent circuit schematic



● **Electrical characteristics (T_C =25°C unless otherwise specified)**

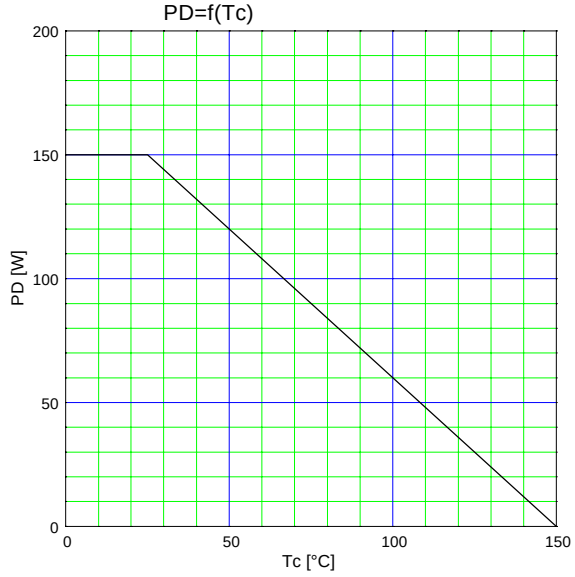
Item	Symbol	Test Conditions		Min.	Typ.	Max.	Units
Drain-source breakdown voltaget	BV_{DSS}	I_D=1mA V_{GS}=0V		60			V
Gate threshold voltage	$V_{GS(th)}$	I_D=10mA V_{DS}=V_{GS}		2.5	3.0	3.5	V
Zero gate voltage drain current	I_{DSS}	V_{DS}=60V	T_{ch}=25°C		10	500	μA
		V_{GS}=0V	T_{ch}=125°C		0.2	1.0	mA
Gate-source leakage current	I_{GSS}	V_{GS}=±30V V_{DS}=0V			10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	I_D=50A V_{GS}=10V			5.7	7.8	mΩ
Forward transcondutance	g_{fs}	I_D=50A V_{DS}=25V		25	55		S
Input capacitance	C_{iss}	V_{DS}=25V			5400	8100	pF
Output capacitance	C_{oss}	V_{GS}=0V			2100	3150	
Reverse transfer capacitance	C_{rss}	f=1MHz			550	830	
Turn-on time t_{on}	$t_{d(on)}$	V_{CC}=30V I_D=100A			29	50	ns
	t_r	V_{GS}=10V			200	350	
Turn-off time t_{off}	$t_{d(off)}$	R_{GS}=10Ω			160	240	
	t_f				150	230	
Avalanche capability	I_{AV}	L=100 μH T_{ch}=25°C		100			A
Diode forward on-voltage	V_{SD}	I_F=100A V_{GS}=0V T_{ch}=25°C			1.0	1.5	V
Reverse recovery time	t_{rr}	I_F=50A V_{GS}=0V			85		ns
Reverse recovery charge	Q_{rr}	-di/dt=100A/μs T_{ch}=25°C			0.21		μC

● **Thermalcharacteristics**

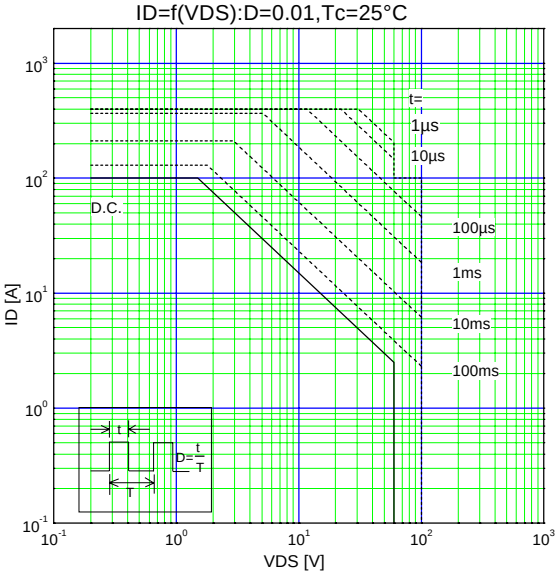
Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(ch-c)}$	channel to case			0.83	°C/W
	$R_{th(ch-a)}$	channel to ambient			35.0	°C/W

Characteristics

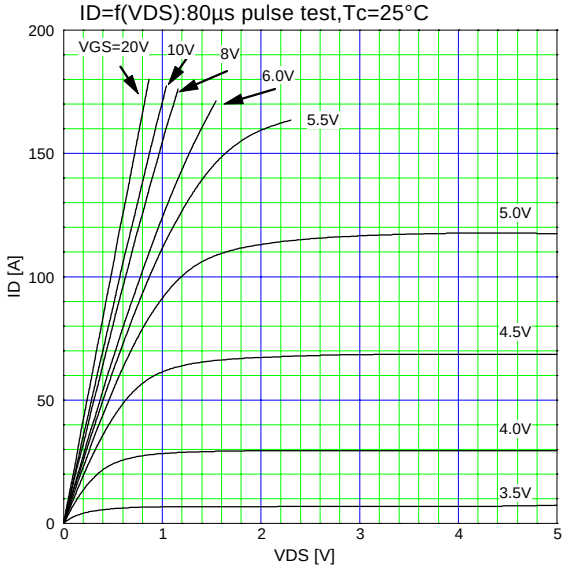
Power Dissipation
PD=f(Tc)



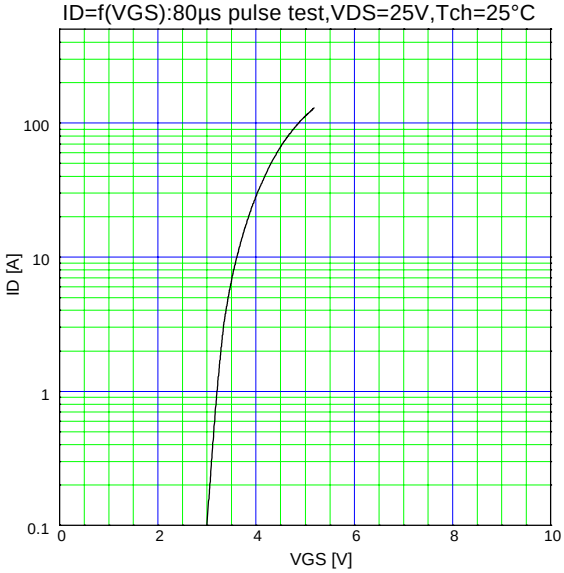
Safe operating area
ID=f(VDS):D=0.01,Tc=25°C



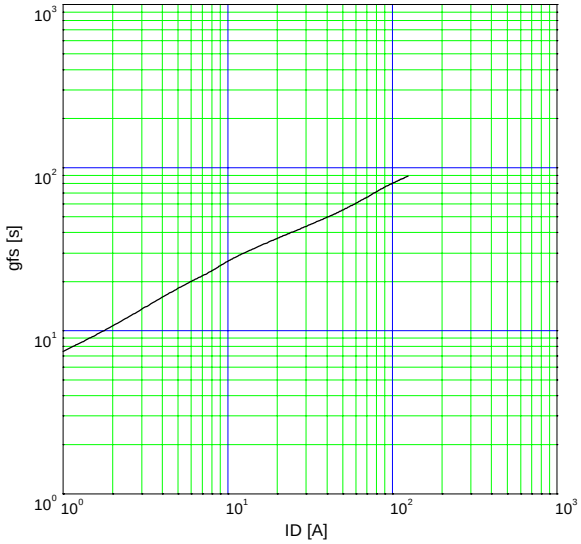
Typical output characteristics
ID=f(VDS):80µs pulse test,Tc=25°C



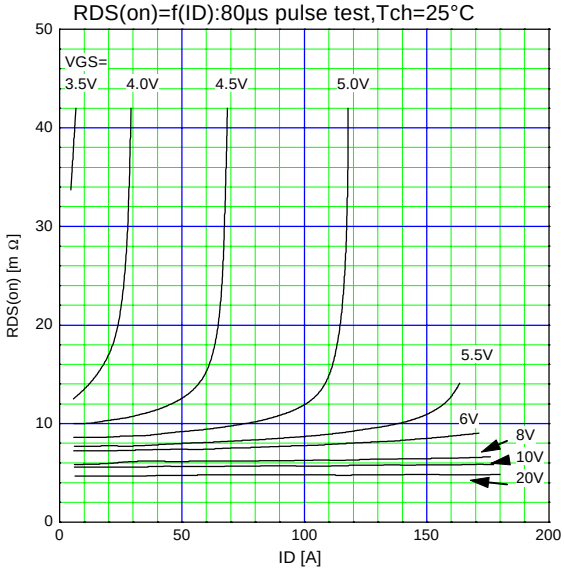
Typical transfer characteristics
ID=f(VGS):80µs pulse test,VDS=25V,Tch=25°C



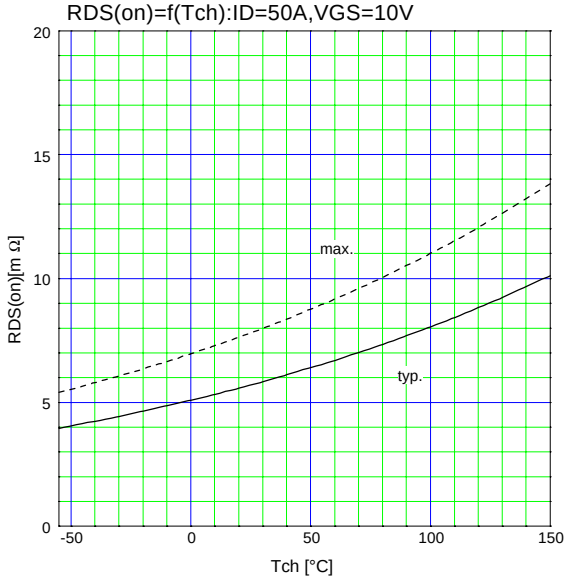
Typical forward transconductance
gfs=f(ID):80µs pulse test,VDS=25V,Tch=25°C



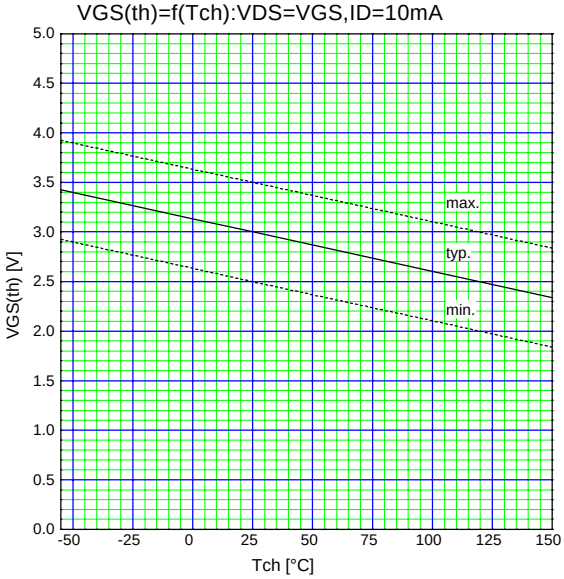
Typical Drain-Source on-State Resistance
RDS(on)=f(ID):80µs pulse test,Tch=25°C



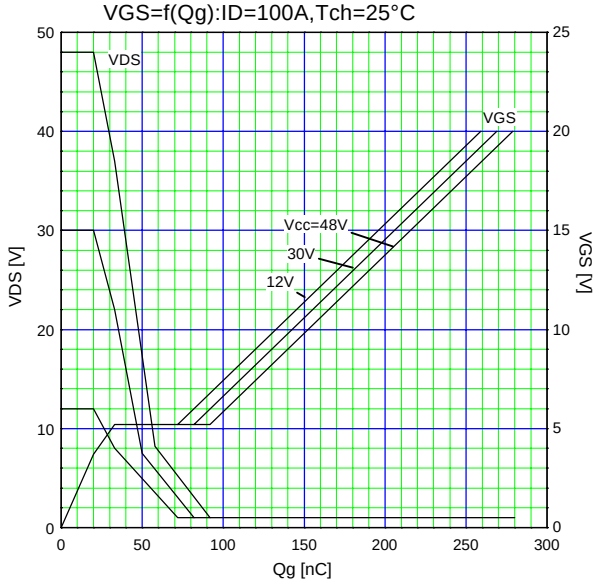
Drain-source on-state resistance
RDS(on)=f(Tch):ID=50A,VGS=10V



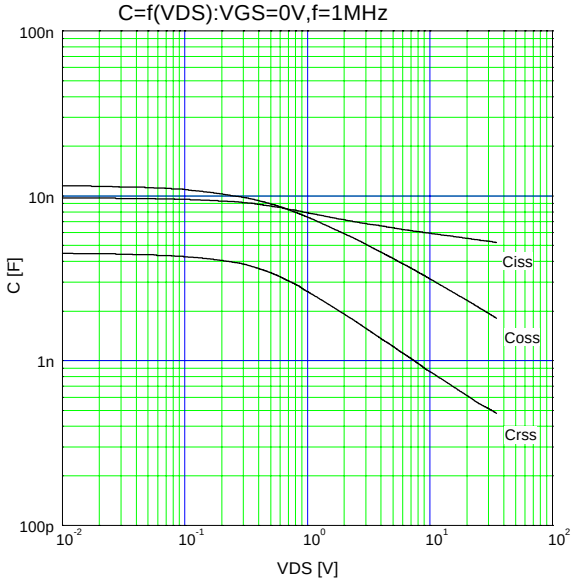
Gate Threshold Voltage vs. Tch
VGS(th)=f(Tch):VDS=VGS,ID=10mA



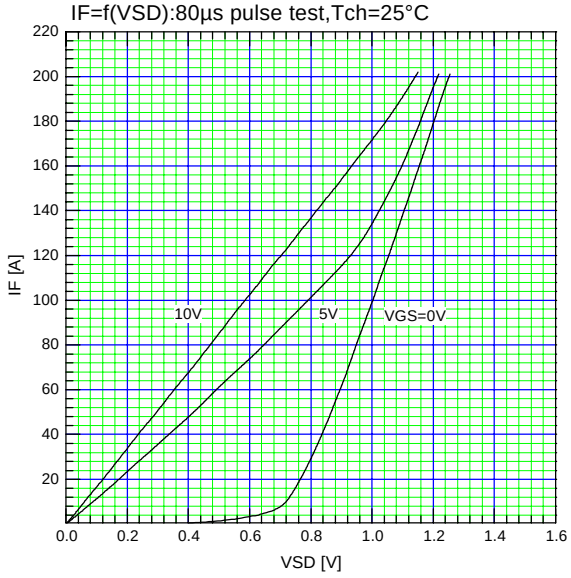
Typical Gate Charge Characteristics
VGS=f(Qg):ID=100A,Tch=25°C



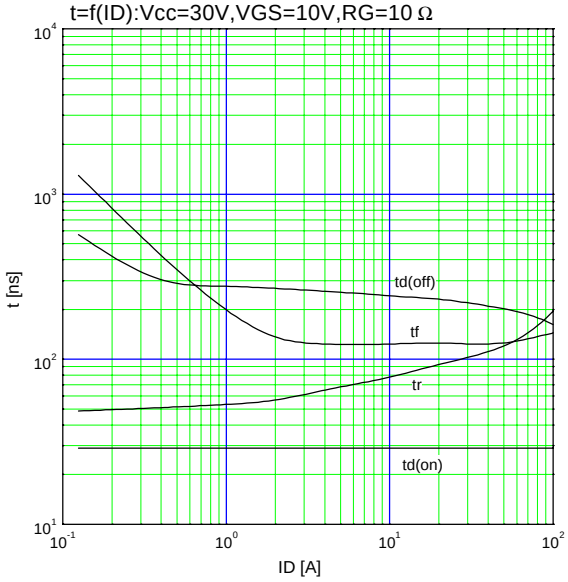
Typical capacitances
C=f(VDS):VGS=0V,f=1MHz



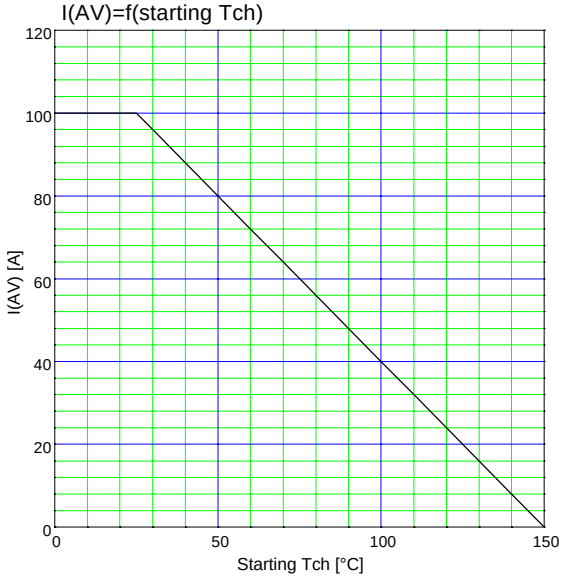
Typical Forward Characteristics of Reverse Diode
IF=f(VSD):80µs pulse test,Tch=25°C



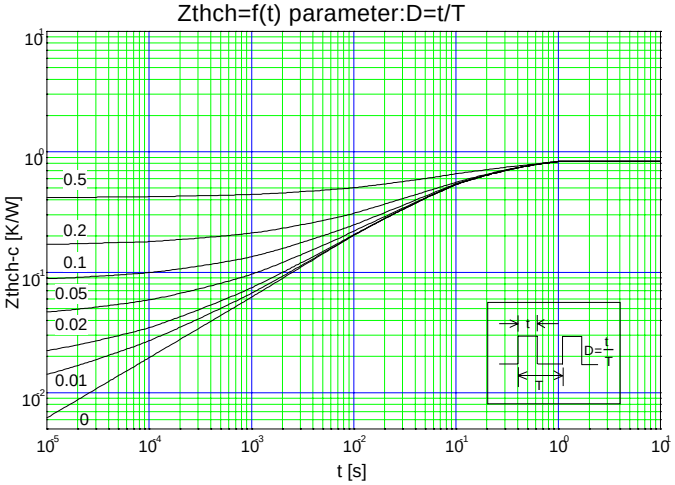
Typical Switching Characteristics vs. ID
t=f(ID):Vcc=30V,VGS=10V,RG=10 Ω



Maximum Avalanche Current vs. starting Tch
I(AV)=f(starting Tch)



Transient thermal impedande
Zthch=f(t) parameter:D=t/T



Maximum Avalanche energy vs. starting Tch
Eas=f(starting Tch):Vcc=24V, I(AV)<=100A